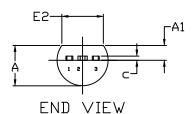
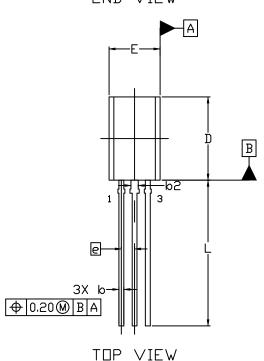


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STRAIGHT LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Δ	3.75	3.90	4.05		
A1	1.28	1.43	1.58		
Ø	0.38	0.465	0.55		
ρQ	0.62	0.70	0.78		
C	0.35	0.40	0.45		
D	7.85	8.00	8.15		
E	4.75	4.90	5.05		
E2	3.90	3.90			
е	1.27 BSC				
L	13.80 14.00 14.20				

STYLES AND MARKING ON PAGE 3

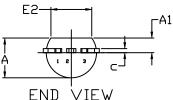
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DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 1 OF 3			

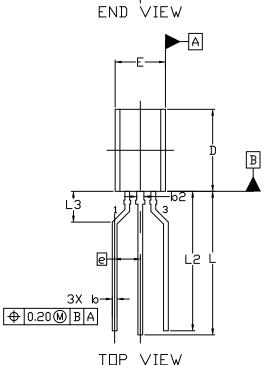
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DATE 05 MAR 2021

FORMED LEAD





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS					
DIM	MIN.	N□M.	MAX.			
Α	3.75	3.90	4.05			
A1	A1 1.28 1.43		1.58			
b	0.38	0.465	0.55			
b2	0.62	0.62 0.70 0.7				
С	0.35	0.40	0.45			
D	7.85	7.85 8.00				
Е	4.75	4.90	5.05			
E2	3.90					
е	2.50 BSC					
L	13.80	14.00	14.20			
L2	13.20	13.60	14.00			
L3	3.00 REF					

STYLES AND MARKING ON PAGE 3

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STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1. 2.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
	CATE	DIM 4		2.	DRAIN	PIN 1. 2.		2.	CATHODE GATE ANODE
2.	CATHODE & ANODE	2.		2.	ANODE 1	2.	EMITTER		
2.	ANODE	PIN 1	COLLECTOR BASE EMITTER	PIN 1	ANODE	2.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
2.			GATE	PIN 1. 2.	GATE	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	
	V _{CC}	2.	MT	2.	CATHODE	PIN 1. 2.	NOT CONNECTED ANODE CATHODE		DRAIN GATE SOURCE
		STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC		

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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